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APPLICATION NO).	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
10/642,929		08/18/2003	Kenji Sakai	2281.2.15	3856
21552	7590	02/09/2006		EXAMINER	
MADSO	N & AUS	STIN	GOUDREAU, GEORGE A		
GATEWA	Y TOWE	R WEST			
SUITE 90	0			ART UNIT	PAPER NUMBER
15 WEST	SOUTH 1	ГЕМРЬЕ	1763		
SALT LAKE CITY, UT 84101				DATE MAIL ED: 02/09/2006	S

Please find below and/or attached an Office communication concerning this application or proceeding.

			X				
	Application No.	Applicant(s)					
	10/642,929	SAKAI ET AL.					
Office Action Summary	Examiner	Art Unit					
	George A. Goudreau	1763	_				
 The MAILING DATE of this communication ap Period for Reply 	pears on the cover sheet w	ith the correspondence address					
A SHORTENED STATUTORY PERIOD FOR REPL WHICHEVER IS LONGER, FROM THE MAILING D. - Extensions of time may be available under the provisions of 37 CFR 1. after SIX (6) MONTHS from the mailing date of this communication. - If NO period for reply is specified above, the maximum statutory period - Failure to reply within the set or extended period for reply will, by statut Any reply received by the Office later than three months after the mailine earned patent term adjustment. See 37 CFR 1.704(b).	DATE OF THIS COMMUNI 136(a). In no event, however, may a will apply and will expire SIX (6) MOI e, cause the application to become A	CATION. reply be timely filed NTHS from the mailing date of this communication. BANDONED (35 U.S.C. § 133).					
Status							
1) Responsive to communication(s) filed on 03 N	November 2005.						
2a)⊠ This action is FINAL 2b)⊠ Thi	This action is FINAL 2b)⊠ This action is non-final.						
	Since this application is in condition for allowance except for formal matters, prosecution as to the merits is						
closed in accordance with the practice under	Ex parte Quayle, 1935 C.	D. 11, 453 O.G. 213.					
Disposition of Claims							
4) Claim(s) 2-10 is/are pending in the application 4a) Of the above claim(s) is/are withdra 5) Claim(s) 2-4 and 7-10 is/are allowed. 6) Claim(s) 5-6 is/are rejected. 7) Claim(s) is/are objected to. 8) Claim(s) are subject to restriction and/o	awn from consideration.						
Application Papers							
9) The specification is objected to by the Examine 10) The drawing(s) filed on is/are: a) acc Applicant may not request that any objection to the Replacement drawing sheet(s) including the correct 11) The oath or declaration is objected to by the E	cepted or b) objected to drawing(s) be held in abeyantion is required if the drawing	nce. See 37 CFR 1.85(a). (s) is objected to. See 37 CFR 1.121(d).					
Priority under 35 U.S.C. § 119							
12) △ Acknowledgment is made of a claim for foreign a) △ All b) ☐ Some * c) ☐ None of: 1. △ Certified copies of the priority documen 2. ☐ Certified copies of the priority documen 3. ☐ Copies of the certified copies of the priority documen application from the International Burea * See the attached detailed Office action for a list	ts have been received. ts have been received in A prity documents have been nu (PCT Rule 17.2(a)).	received in this National Stage	zan				
		GEORGE GOUDREAU PRIMARY EXAMINER	-004				
Attachment(s)	_	2-061					
 Notice of References Cited (PTO-892) Notice of Draftsperson's Patent Drawing Review (PTO-948) 		Summary (PTO-413) s)/Mail Date					
Notice of Draitsperson's Patent Drawing Review (PTO-946) Information Disclosure Statement(s) (PTO-1449 or PTO/SB/08) Paper No(s)/Mail Date	🗖	nformal Patent Application (PTO-152)					

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1. Applicant's arguments with respect to claims of record have been considered but are most in view of the new ground(s) of rejection.

2. Claims 2-4, and 7-10 are allowed.

-H2O2; and

3. The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the basis for the rejections under this section made in this Office action:

A person shall be entitled to a patent unless -

(e) the invention was described in (1) an application for patent, published under section 122(b), by another filed in the United States before the invention by the applicant for patent or (2) a patent granted on an application for patent by another filed in the United States before the invention by the applicant for patent, except that an international application filed under the treaty defined in section 351(a) shall have the effects for purposes of this subsection of an application filed in the United States only if the international application designated the United States and was published under Article 21(2) of such treaty in the English language.

4. Claims 5-6 are rejected under 35 U.S.C. 102(e) as being anticipated by Tsai et. al. (6,524,167).

Tsai et. al. disclose a process for forming a Cu damascene structure on the surface of a wafer. A damascene hole in an insulating layer on the surface of a wafer is filled with a Cu layer, and a Ta barrier layer. The Cu layer, and the Ta barrier layer are then cmp polished using a cmp slurry, which is comprised of the following components:

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-H2O;
-abrasive particules (i.e.-silica, alumina, etc.);
-an anticorrosive agent (i.e.-BTA, etc.);
-a pH-adjusting agent (i.e.-potassium hydroxide, phosphoric acid, acetic acid, etc.);
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-a chelating agent (i.e.-polishing accelerator such as glycine, etc.)

This is discussed specifically in columns 9-12; and is discussed in general in columns 1-12. This is shown in figures 1-4.

The process taught above could be considered a three-step process in which the first step, the second step, and the third step are all the same. Thus, all of applicant's claimed limitations are fully met in these regards.

5. Claims 5-6 are rejected under 35 U.S.C. 102(e) as being anticipated by Asano et. al. (6,679,929).

Asano et. al. disclose a process for forming a Cu damascene structure on the surface of a wafer. A damascene hole in an insulating layer on the surface of a wafer is filled with a Cu layer, and a Ta barrier layer. The Cu layer, and the Ta barrier layer are then cmp polished using a cmp slurry, which is comprised of the following components:

- -H2O;
- -abrasive particules (i.e.-silica, alumina, etc.);
- -an anticorrosive agent (i.e.-BTA, etc.);
- -H2O2; and
- -a polishing accelerator (i.e.-citric acid, oxalic acid, tartaric acid, glycine, etc.)

This is discussed specifically in columns 1-3; and is discussed in general in columns 1-14.

The process taught above could be considered a three-step process in which the first step, the second step, and the third step are all the same. Thus, all of applicant's claimed limitations are fully met in these regards.

6. Applicant's amendment necessitated the new ground(s) of rejection presented in this Office action. Accordingly, **THIS ACTION IS MADE FINAL**. See MPEP § 706.07(a). Applicant is reminded of the extension of time policy as set forth in 37 CFR 1.136(a).

A shortened statutory period for reply to this final action is set to expire THREE MONTHS from the mailing date of this action. In the event a first reply is filed within TWO MONTHS of the mailing date of this final action and the advisory action is not mailed until after the end of the THREE-MONTH shortened statutory period, then the shortened statutory period will expire on the date the advisory action is mailed, and any extension fee pursuant to 37 CFR 1.136(a) will be calculated from the mailing date of the advisory action. In no event, however, will the statutory period for reply expire later than SIX MONTHS from the date of this final action.

7. Any inquiry concerning this communication should be directed to examiner George A. Goudreau at telephone number (571)-272-1434.

George A. Goudreau

Printary Examiner

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